

DMN26D0UFB4

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

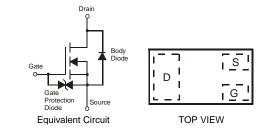
- N-Channel MOSFET
- Low On-Resistance:
 - 3.0 Ω @ 4.5V
 - 4.0 Ω @ 2.5V •
 - 6.0 Ω @ 1.8V •
 - 10 Ω @ 1.5V
- Very Low Gate Threshold Voltage, 1.2V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN1006H4-3
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper leadframe. Solderable • per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.001 grams (approximate)







Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±10	V
Drain Current (Note 1)		ID	230	mA
Pulsed Drain Current	$T_P = 10 \mu s$	I _{DM}	805	mA

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Thermal Characteristics @T_A = 25°C unless otherwise specified

Total Power Dissipation (Note 1) $@T_A = 25^{\circ}C$	PD	350	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ ext{ heta}JA}$	357	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: Device mounted on FR-4 PCB, pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at 1. http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead.

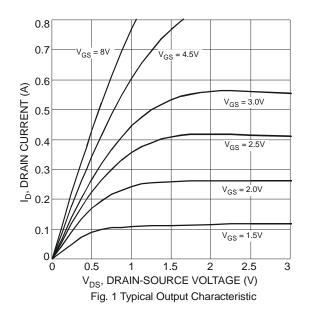
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

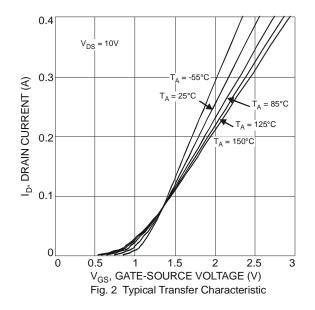


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Sumbol	Min	Turn	Max	Unit	Test Condition
		Symbol	WIIN	Тур	wax	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)				1			
Drain-Source Breakdown Voltage		BV _{DSS}	20	_		V	$V_{GS} = 0V, I_D = 100\mu A$
Zero Gate Voltage Drain Current	@ T _C = 25°C	I _{DSS}	_		500	nA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}			±1	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
		.633			±100	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage		V _{GS(th)}	0.6		0.9	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
				1.8	3.0	Ω	$V_{GS} = 4.5V, I_D = 100mA$
			_	2.4	4.0		$V_{GS} = 2.5V, I_D = 50mA$
Static Drain-Source On-Resistance		R _{DS (ON)}	_	2.9	6.0		$V_{GS} = 1.8V, I_{D} = 20mA$
			_	3.7	10.0		V _{GS} = 1.5V, I _D = 10mA
			—	5.4	15.0		$V_{GS} = 1.2V, I_{D} = 1mA$
Forward Transconductance		Y _{fs}	100	242	_	mS	$V_{DS} = 10V, I_D = 0.1A$
Source-Drain Diode Forward Voltage		V _{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS							
Input Capacitance		Ciss	_	14.1	_	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance		Coss		2.9	_	pF	
Reverse Transfer Capacitance		Crss	_	1.6		pF	
SWITCHING CHARACTERISTICS							
Turn-On Time		T _{ON}	—	12	—	ns	$V_{GS} = 4.5V, V_{DD} = 10V$
Turn-Off Time		T _{OFF}		29		115	$I_D = 200 \text{mA}, R_G = 2.0 \Omega$

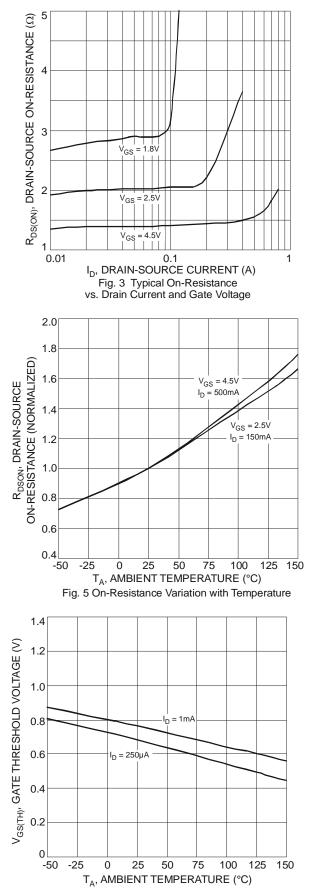
Notes: 4. Short duration pulse test used to minimize self-heating effect.

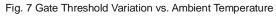


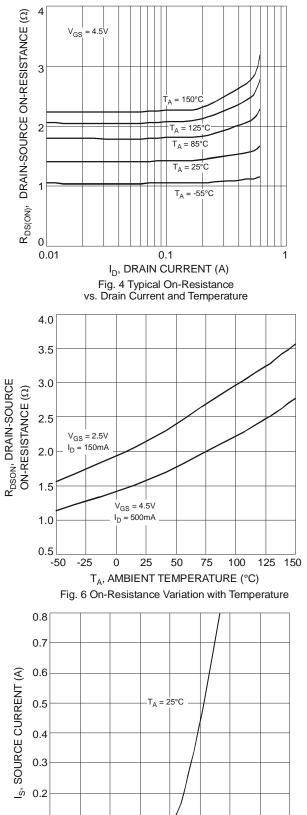


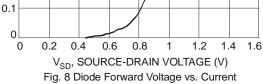
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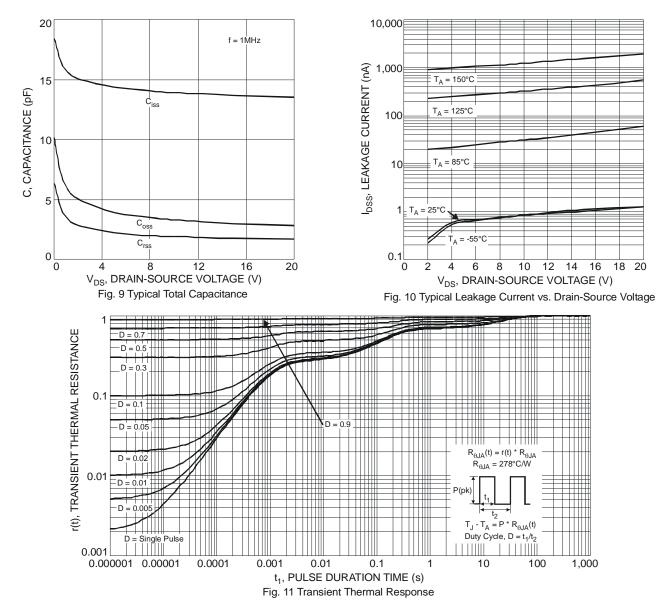






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Ordering Information (Note 5)

Part Number	Case	Packaging
DMN26D0UFB4-7	DFN1006H4-3	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

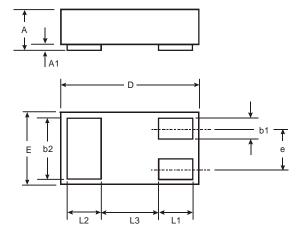
Marking Information



M1 = Product Type Marking Code

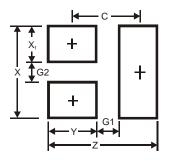


Package Outline Dimensions



DFN1006H4-3				
Dim	Min	Max	Тур	
Α		0.40	_	
A1	0	0.05	0.02	
b1	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.05	1.00	
ш	0.55	0.65	0.60	
е	_	_	0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3			0.40	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Y	0.4
С	0.7



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